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ON Semiconductor®

FQD3P50TM-F085

500V P-Channel MOSFET

General Description

These P-Channel enhancement mode power field effect transistors are produced using ON Semiconductor's proprietary, planar stripe, DMOS technology.
This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for electronic lamp ballast based on complimentary half bridge.

Features

- -2.1A, -500V, $R_{DS(on)}$ = 4.9Ω @V_{GS} = -10 V
- Low gate charge (typical 18 nC)
- Low Crss (typical 9.5 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- Qualified to AEC Q101
- RoHS Compliant

100% LEAD-FREE IMPLEMENTATION

D-PAK
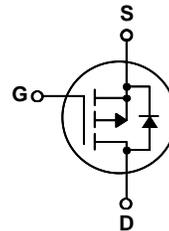
Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter		FQD3P50TM-F085	Units
V_{DSS}	Drain-Source Voltage		-500	V
I_D	Drain Current - Continuous (T_C = 25°C)		-2.1	A
	- Continuous (T_C = 100°C)		-1.33	A
I_{DM}	Drain Current - Pulsed	(Note 1)	-8.4	A
V_{GSS}	Gate-Source Voltage		± 30	V
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	250	mJ
I_{AR}	Avalanche Current	(Note 1)	-2.1	A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	5.0	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	-4.5	V/ns
P_D	Power Dissipation (T_A = 25°C) *		2.5	W
	Power Dissipation (T_C = 25°C)		50	W
	- Derate above 25°C		0.4	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	2.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient *	--	50	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	110	°C/W

* When mounted on the minimum pad size recommended (PCB Mount)

Elerical Characteristics
T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = -250 µA	-500	--	--	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = -250 µA, Referenced to 25°C	--	0.42	--	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = -500 V, V_{GS} = 0 V	--	--	-1	µA
		V_{DS} = -400 V, T_C = 125°C	--	--	-10	µA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = -30 V, V_{DS} = 0 V	--	--	-100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = 30 V, V_{DS} = 0 V	--	--	100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = -250 µA	-3.0	--	-5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = -10 V, I_D = -1.05 A	--	3.9	4.9	Ω
g_{FS}	Forward Transconductance	V_{DS} = -50 V, I_D = -1.05 A (Note 4)	--	2.1	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = -25 V, V_{GS} = 0 V, f = 1.0 MHz	--	510	660	pF
C_{oss}	Output Capacitance		--	70	90	pF
C_{rss}	Reverse Transfer Capacitance		--	9.5	12	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = -250 V, I_D = -2.7 A, R_G = 25 Ω	--	12	35	ns
t_r	Turn-On Rise Time		--	56	120	ns
$t_{d(off)}$	Turn-Off Delay Time		--	35	80	ns
t_f	Turn-Off Fall Time	(Note 4, 5)	--	45	100	ns
Q_g	Total Gate Charge	V_{DS} = -400 V, I_D = -2.7 A, V_{GS} = -10 V	--	18	23	nC
Q_{gs}	Gate-Source Charge		--	3.6	--	nC
Q_{gd}	Gate-Drain Charge	(Note 4, 5)	--	9.2	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	-2.1	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	-8.4	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = -2.1 A	--	--	-5.0	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_S = -2.7 A,	--	270	--	ns
Q_{rr}	Reverse Recovery Charge	dI_F / dt = 100 A/µs (Note 4)	--	1.5	--	µC

Notes:
1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 102mH, I_{AS} = -2.1A, V_{DD} = -50V, R_G = 25 Ω, Starting T_J = 25°C
3. I_{SD} ≤ -2.7A, di/dt ≤ 200A/µs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Pulse Test : Pulse width ≤ 300µs, Duty cycle ≤ 2%
5. Essentially independent of operating temperature

FQD3P50TM-F085   500V P-Channel MOSFET

Typical Characteristics
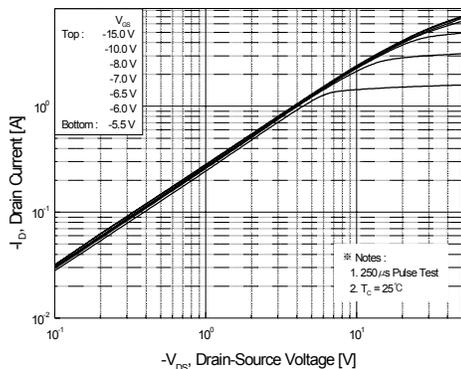
**Figure 1. On-Region Characteristics**
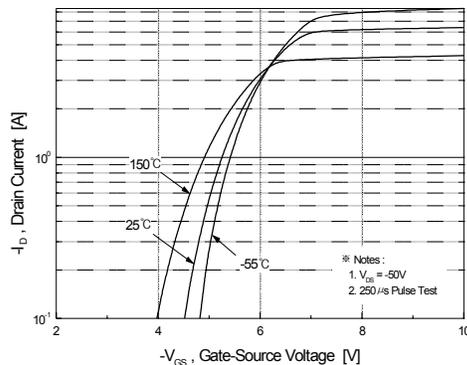
**Figure 2. Transfer Characteristics**
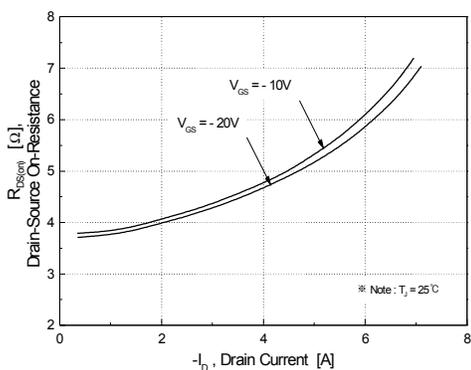
Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage
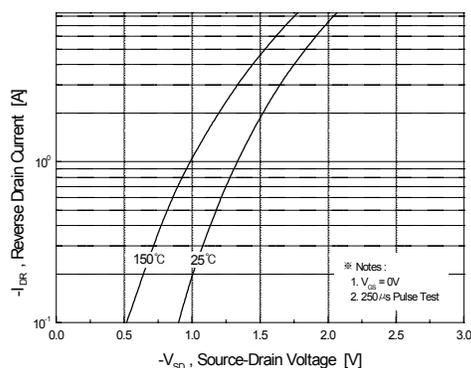

**Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature**
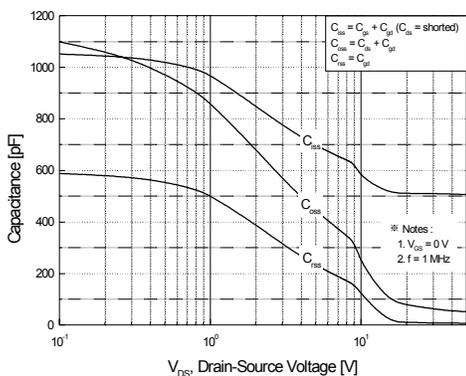

Figure 5. Capacitance Characteristics
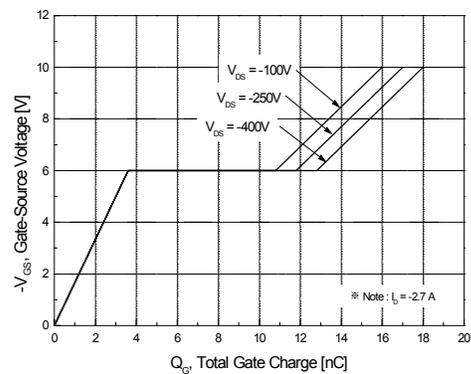

Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)
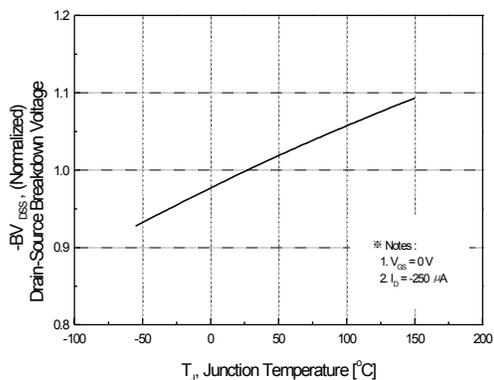
Figure 7. Breakdown Voltage Variation vs. Temperature
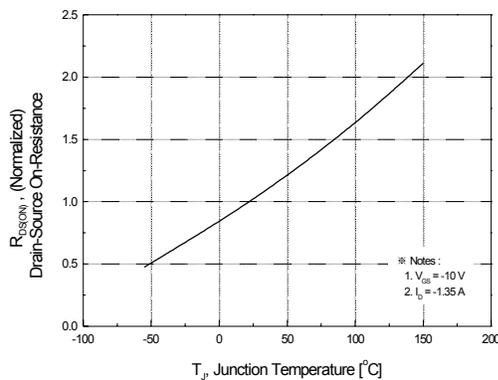
Figure 8. On-Resistance Variation vs. Temperature
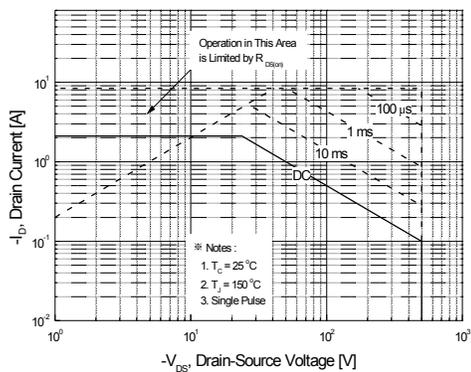
Figure 9. Maximum Safe Operating Area
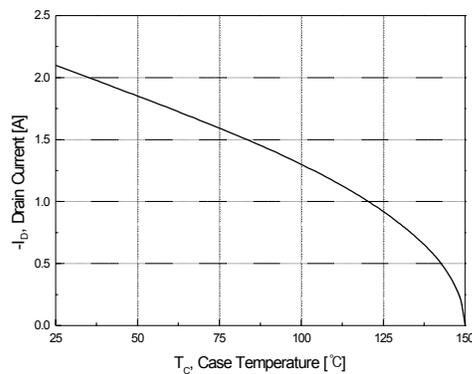
Figure 10. Maximum Drain Current vs. Case Temperature
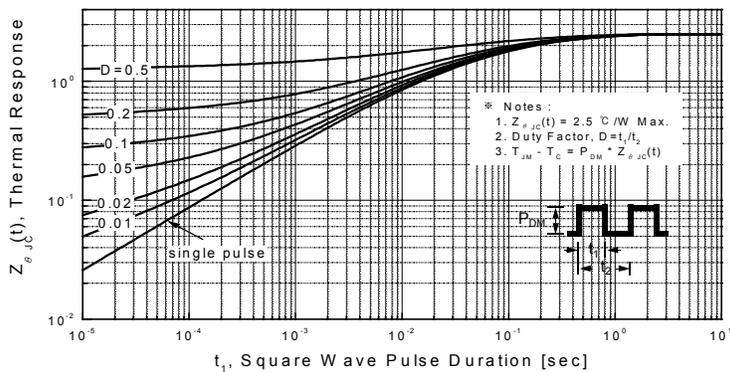
Figure 11. Transient Thermal Response Curve

Gate Charge Test Circuit & Waveform
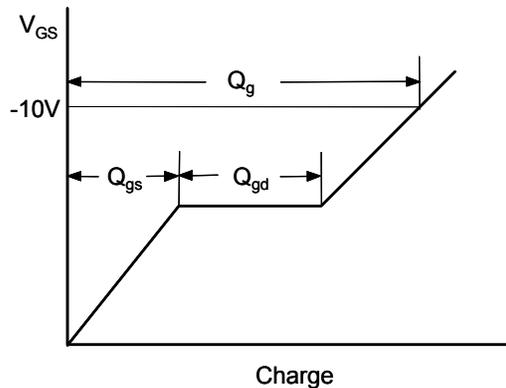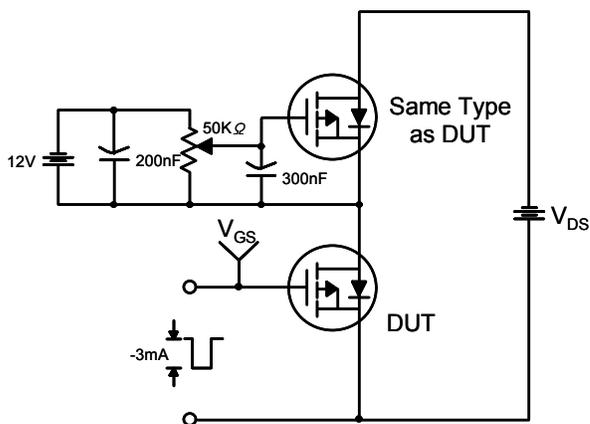
Resistive Switching Test Circuit & Waveforms
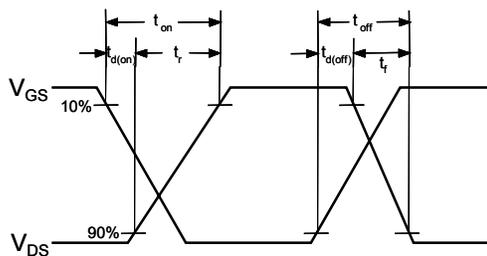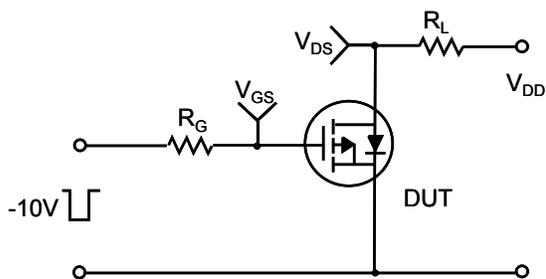
Unclamped Inductive Switching Test Circuit & Waveforms

$$E_{AS} = \frac{1}{2} L I_{AS}^2 \; \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$
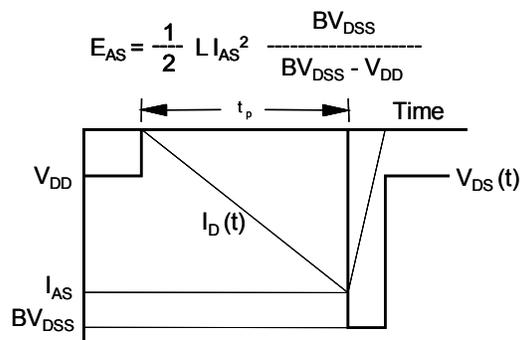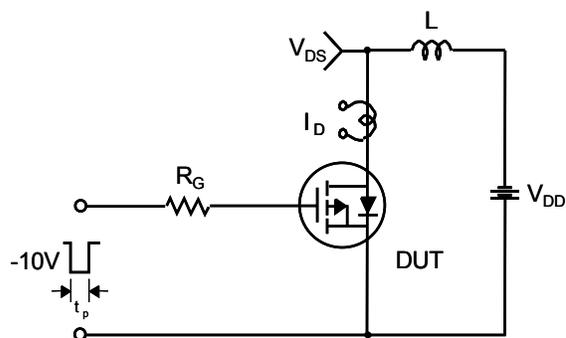
Peak Diode Recovery dv/dt Test Circuit & Waveforms

V_{DS}

DUT

I_{SD}

L

Driver

R_G

Compliment of DUT
(N-Channel)

V_{DD}

V_{GS}

• dv/dt controlled by R_G
• I_{SD} controlled by pulse period

V_{GS}
(Driver)

$$D = \frac{\text{Gate Pulse Width}}{\text{Gate Pulse Period}}$$

10V

I_{SD}
(DUT)

Body Diode Reverse Current

I_{RM}

di/dt

I_{FM} , Body Diode Forward Current

V_{DS}
(DUT)

V_{SD}

Body Diode
Forward Voltage Drop

V_{DD}

Body Diode Recovery dv/dt
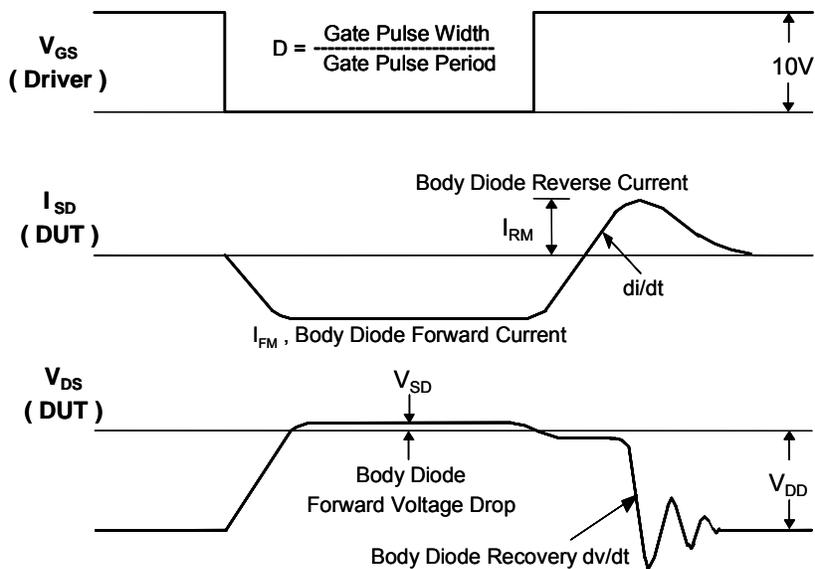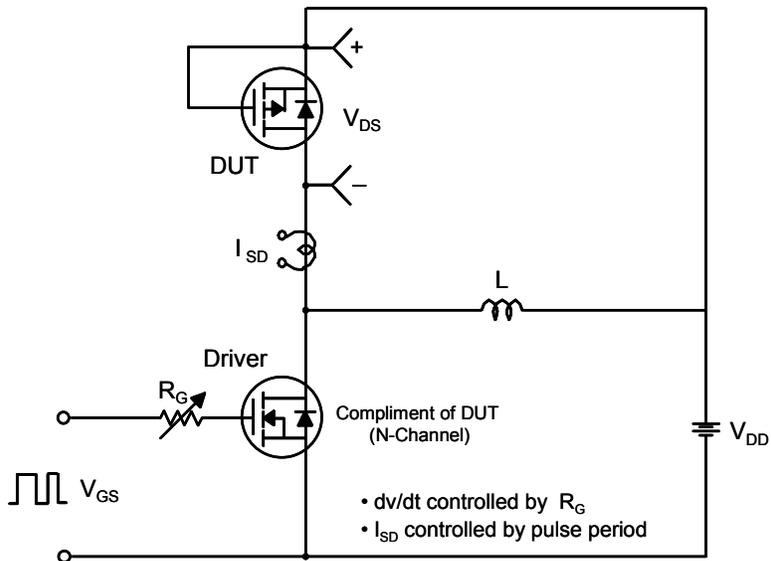
Mechanical Dimensions

TO-252 (DPAK) (FS PKG Code 36)

1:1
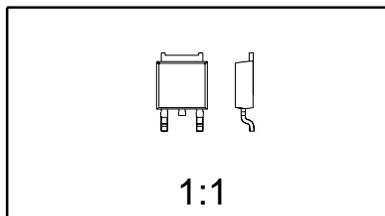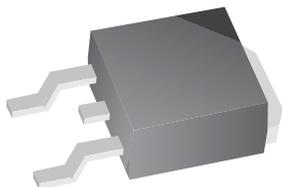
Scale 1:1 on letter size paper

Dimensions shown below are in:
millimeters

Part Weight per unit (gram): 0.33
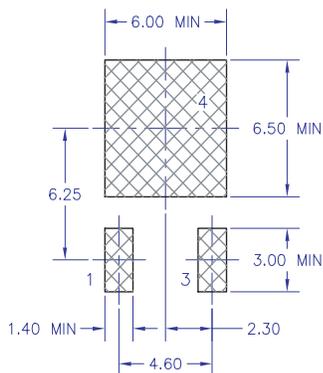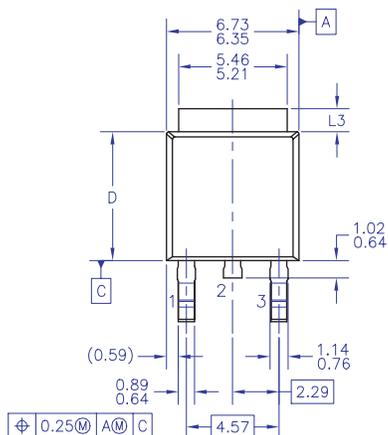
LAND PATTERN RECOMMENDATION

DETAIL A
(ROTATED −90°)
SCALE: 12X
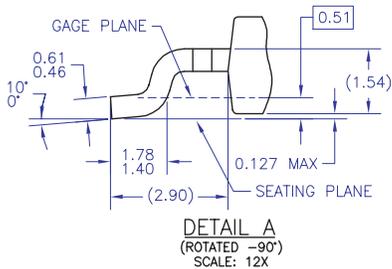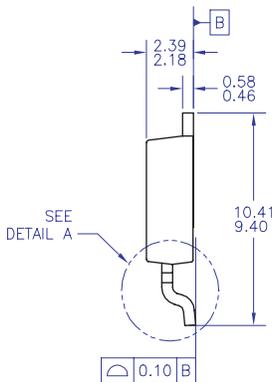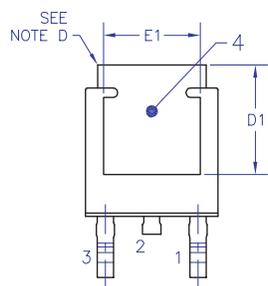
NOTES: UNLESS OTHERWISE SPECIFIED
A) ALL DIMENSIONS ARE IN MILLIMETERS.
B) THIS PACKAGE CONFORMS TO JEDEC, TO−252,
    ISSUE C, VARIATION AA & AB, DATED NOV. 1999.
C) DIMENSIONING AND TOLERANCING PER
    ASME Y14.5M−1994.
D) HEAT SINK TOP EDGE COULD BE IN CHAMFERED
    CORNERS OR EDGE PROTRUSION.
E) DIMENSIONS L3,D,E1&D1 TABLE:

	OPTION AA	OPTION AB
L3	0.89−1.27	1.52−2.03
D	5.97−6.22	5.33−5.59
E1	4.32 MIN	3.81 MIN
D1	5.21 MIN	4.57 MIN

PUBLICATION ORDERING INFORMATION

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